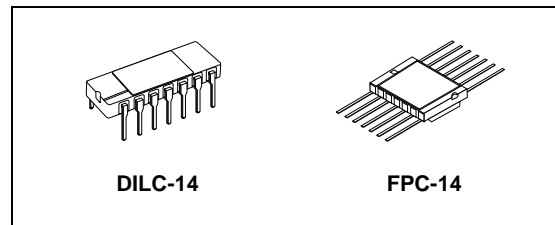


RAD-HARD TRIPLE 3-INPUT AND GATE

- HIGH SPEED:
 $t_{PD} = 9\text{ns}$ (TYP.) at $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:
 $I_{CC} = 1\mu\text{A}$ (MAX.) at $T_A=25^\circ\text{C}$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 4\text{mA}$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH
 54 SERIES 11
- SPACE GRADE-1: ESA SCC QUALIFIED
- 50 krad QUALIFIED, 100 krad AVAILABLE ON
 REQUEST
- NO SEL UNDER HIGH LET HEAVY IONS
 IRRADIATION
- DEVICE FULLY COMPLIANT WITH
 SCC-9201-107



ORDER CODES

PACKAGE	FM	EM
DILC	M54HC11D	M54HC11D1
FPC	M54HC11K	M54HC11K1

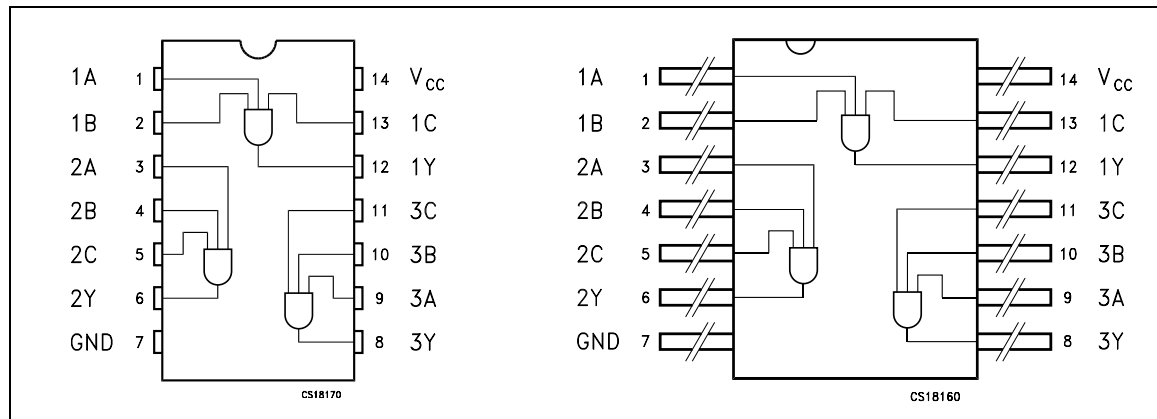
The internal circuit is composed of 4 stages including buffer output, which enables high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

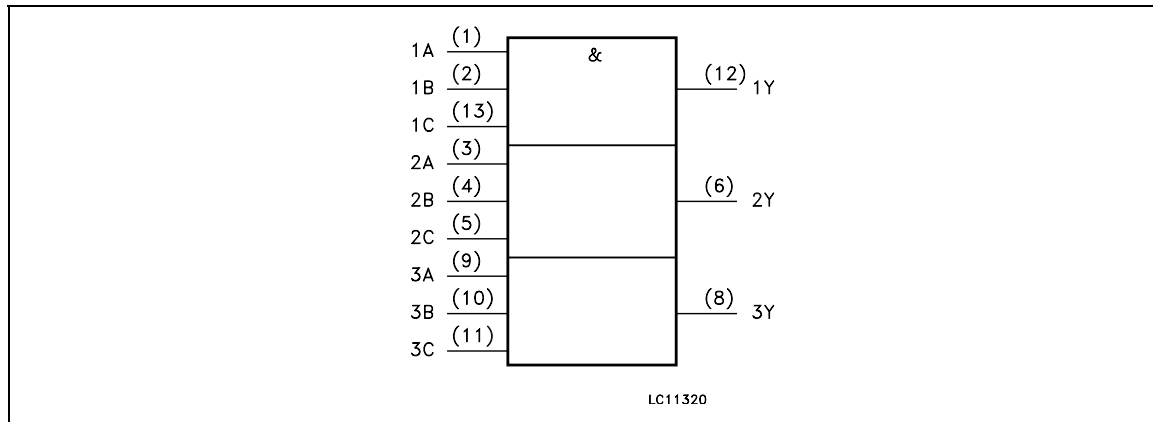
DESCRIPTION

The M54HC11 is an high speed CMOS TRIPLE 3-INPUT AND GATE fabricated with silicon gate C²MOS technology.

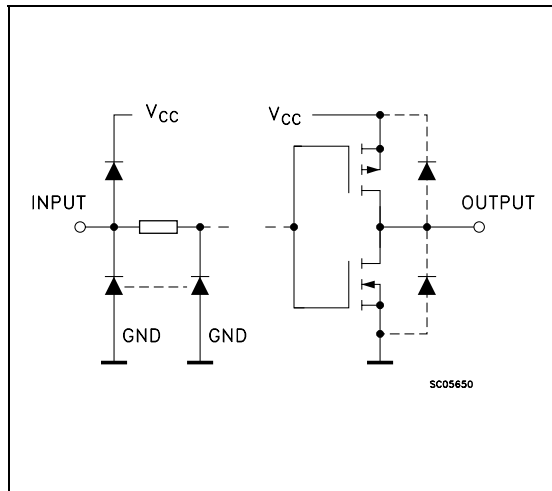
PIN CONNECTION



IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
1, 3, 9	1A to 3A	Data Inputs
2, 4, 10	1B to 3B	Data Inputs
13, 5, 11	1C to 3C	Data Inputs
12, 6, 8	1Y to 3Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	B	C	Y
L	X	X	L
X	L	X	L
X	X	L	L
H	H	H	H

X : Don't Care

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	300	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	265	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage	2 to 6	V	
V_I	Input Voltage	0 to V_{CC}	V	
V_O	Output Voltage	0 to V_{CC}	V	
T_{op}	Operating Temperature	-55 to 125	°C	
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
				$T_A = 25^\circ C$			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V_{IH}	High Level Input Voltage	V_{CC} (V)		1.5			1.5		1.5	V	
				3.15			3.15		3.15		
				4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	V_{CC} (V)				0.5		0.5		0.5	V
						1.35		1.35		1.35	
						1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	V_{CC} (V)	$I_O = -20 \mu A$	1.9	2.0		1.9		1.9	V	
			$I_O = -20 \mu A$	4.4	4.5		4.4		4.4		
			$I_O = -20 \mu A$	5.9	6.0		5.9		5.9		
			$I_O = -4.0 mA$	4.18	4.31		4.13		4.10		
			$I_O = -5.2 mA$	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	V_{CC} (V)	$I_O = 20 \mu A$		0.0	0.1		0.1		0.1	V
			$I_O = 20 \mu A$		0.0	0.1		0.1		0.1	
			$I_O = 20 \mu A$		0.0	0.1		0.1		0.1	
			$I_O = 4.0 mA$		0.17	0.26		0.33		0.40	
			$I_O = 5.2 mA$		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		μA	
I_{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			1		10		20	μA

M54HC11

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

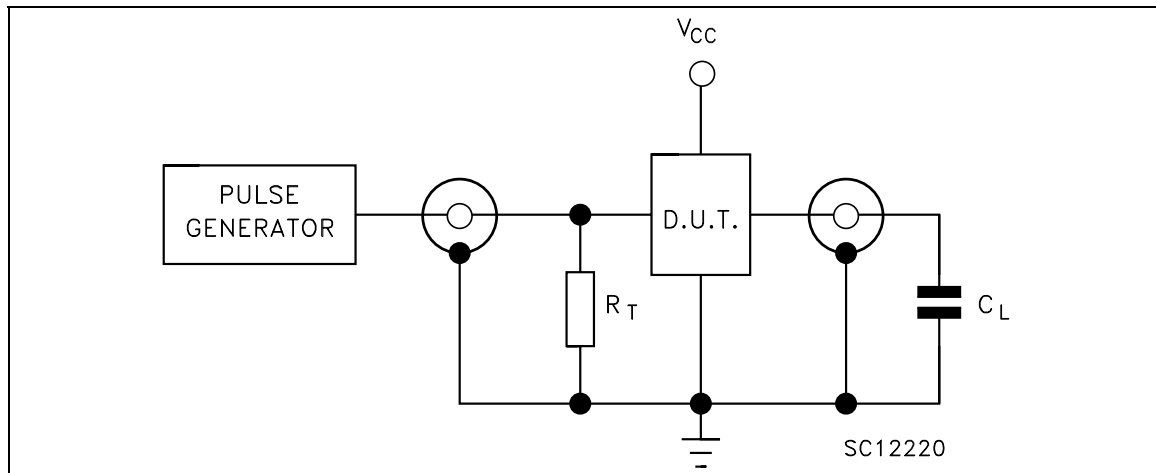
Symbol	Parameter	Test Condition		Value						Unit	
				$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				V_{CC} (V)	Min.	Typ.	Max.	Min.	Max.		Min.
t_{TLH} t_{THL}	Output Transition Time	2.0		30	75		95		110	ns	
		4.5		8	15		19		22		
		6.0		7	13		16		19		
t_{PLH} t_{PHL}	Propagation Delay Time	2.0		40	85		105		130	ns	
		4.5		10	17		21		26		
		6.0		9	14		18		22		

CAPACITIVE CHARACTERISTICS

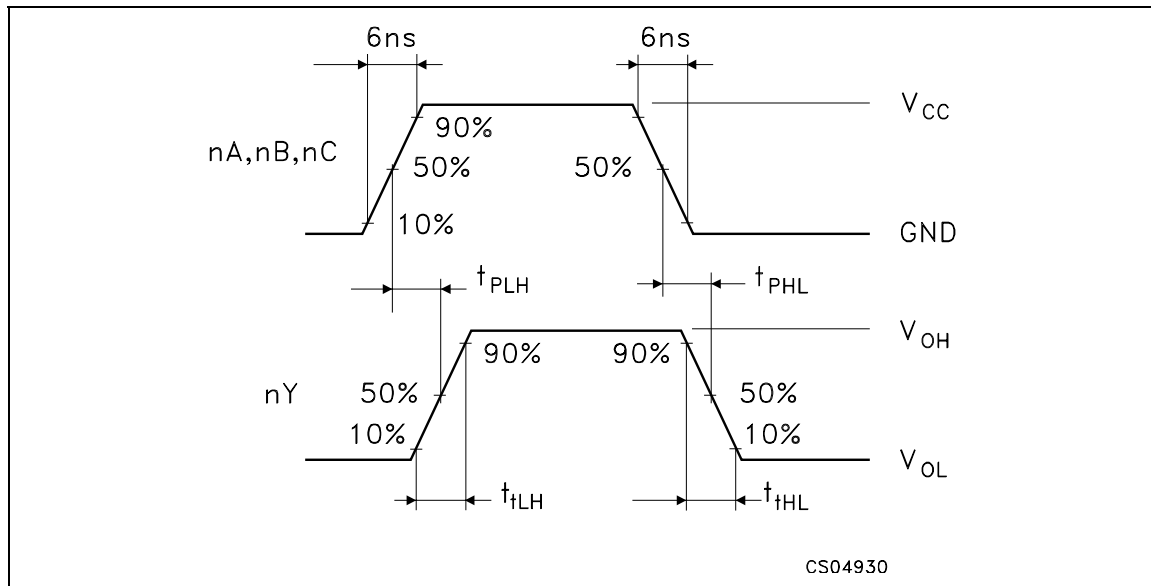
Symbol	Parameter	Test Condition		Value						Unit	
				$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				V_{CC} (V)	Min.	Typ.	Max.	Min.	Max.		Min.
C_{IN}	Input Capacitance	5.0		5	10		10		10	pF	
C_{PD}	Power Dissipation Capacitance (note 1)	5.0		26						pF	

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/3$ (per gate)

TEST CIRCUIT

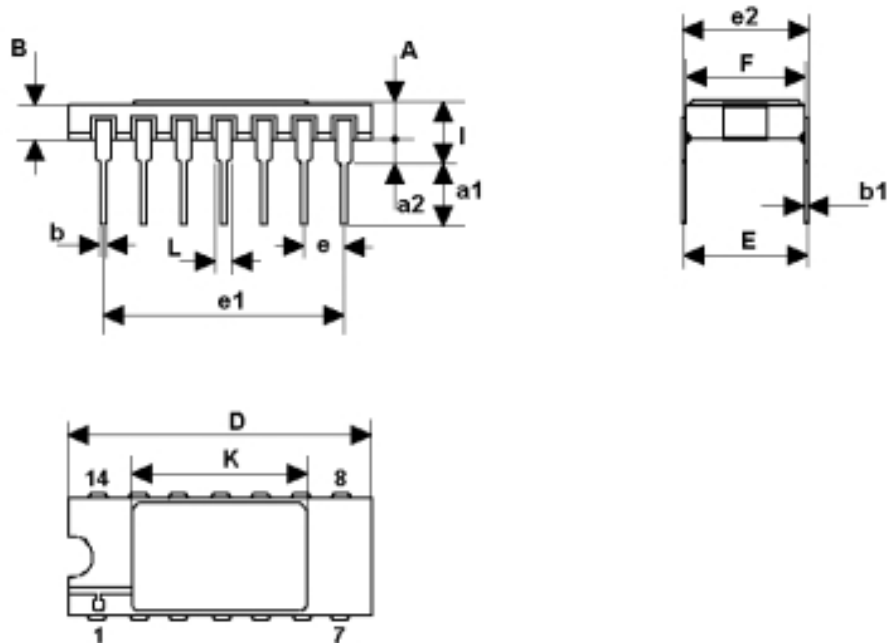


$C_L = 50 \text{ pF}$ or equivalent (includes jig and probe capacitance)
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAY TIME ($f=1\text{MHz}$; 50% duty cycle)

DILC-14 MECHANICAL DATA

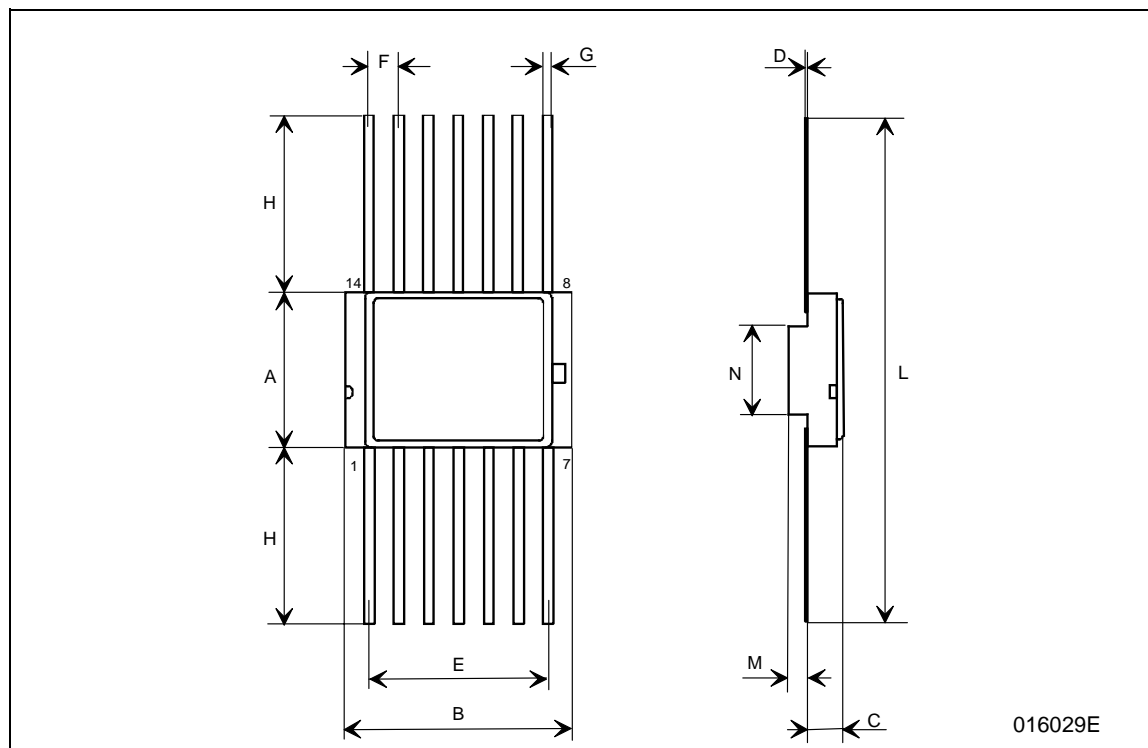
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.1		22.54	0.083		0.100
a1	3.00		3.70	0.118		0.146
a2	0.63	0.88	1.14	0.025	0.035	0.045
B	1.82	2.03	2.39	0.072	0.080	0.094
b	0.40	0.45	0.50	0.016	0.018	0.020
b1	0.20	0.254	0.30	0.008	0.010	0.012
D	18.79	19.00	19.20	0.740	0.748	0.756
e	7.36	7.62	7.87	0.290	0.300	0.310
e1		2.54			0.100	
e2	15.11	15.24	15.37	0.595	0.600	0.605
e3	7.62	7.87	8.12	0.300	0.310	0.320
F	7.11		7.75	0.280		0.305
I			3.70			0.146
K	10.90		12.1	0.429		0.476
L	1.14	1.27	1.5	0.045	0.050	0.059



0016173H

FPC-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	6.75	6.91	7.06	0.266	0.272	0.278
B	9.76	9.95	10.14	0.384	0.392	0.399
C	1.49		1.95	0.059		0.077
D	0.10	0.127	0.15	0.004	0.005	0.006
E	7.50	7.62	7.75	0.295	0.300	0.305
F		1.27			0.050	
G	0.38	0.43	0.48	0.015	0.017	0.019
H		6.0			0.236	
L	18.75		22.0	0.738		0.866
M		0.38			0.015	
N		4.31			0.170	



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